

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q85504

Heiji WATANABE, et al.

Appln. No.: 10/519,084

Group Art Unit: 2822

Confirmation No.: 7332

Examiner: Tsz K. CHIU

Filed: December 23, 2004

For: SEMICONDUCTOR DEVICE AND ITS MANUFACTURING METHOD

INFORMATION DISCLOSURE STATEMENT  
UNDER 37 C.F.R. §§ 1.97 and 1.98

MAIL STOP AMENDMENT

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure under 37 C.F.R. § 1.56, Applicant hereby notifies the U.S. Patent and Trademark Office of the documents which are listed on the attached PTO/SB/08 A & B (modified) form and listed herein and which the Examiner may deem material to patentability of the claims of the above-identified application.

1. H.-J. Cho, et al.: "Novel Nitrogen Profile Engineering for Improved TaN/HfO<sub>2</sub>/Si MOSFET Performance"; IEDM, Technical Digest 2001, pages 655-658 (previously submitted with the Information Disclosure Statement filed December 23, 2004).
2. United States Patent No. 6,380,104, issued April 30, 2002.

Copies of the listed documents are not submitted herewith, as reference 1 has been previously submitted and reference 2 is a U.S. patent. A copy of the corresponding Chinese

INFORMATION DISCLOSURE STATEMENT

U.S. Appln. No.: 10/519,084

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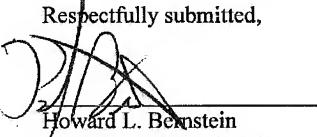
Office Action, dated January 12, 2007, and an English translation thereof, citing the above listed documents is submitted herewith.

The present Information Disclosure Statement is being filed: (1) No later than three months from the application's filing date; (2) Before the mailing date of the first Office Action on the merits (whichever is later); or (3) Before the mailing date of the first Office Action after filing a request for continued examination (RCE) under §1.114, and therefore, no Statement under 37 C.F.R. § 1.97(e) or fee under 37 C.F.R. § 1.17(p) is required.

The submission of the listed documents is not intended as an admission that any such document constitutes prior art against the claims of the present application. Applicant does not waive any right to take any action that would be appropriate to antedate or otherwise remove any listed document as a competent reference against the claims of the present application.

The USPTO is directed and authorized to charge all required fees, except for the Issue Fee and the Publication Fee, to Deposit Account No. 19-4880. Please also credit any overpayments to said Deposit Account.

Respectfully submitted,

  
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WASHINGTON OFFICE

23373

CUSTOMER NUMBER

Date: February 28, 2007

Substitute for Form 1449 A & B/PTO		Complete if Known	
<b><u>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</u></b>		Application Number	10/519,084
(use as many sheets as necessary)		Confirmation Number	7332
		Filing Date	December 23, 2004
		First Named Inventor	Heiji WATANABE
		Art Unit	2822
		Examiner Name	Tsz K. CHIU
Sheet	1	of	1
		Attorney Docket Number	085504

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation <sup>6</sup>
		H.-J. Cho, et al.: "Novel Nitrogen Profile Engineering for Improved TaN/HfO <sub>x</sub> /Si MOSFET Performance", IEDM, Technical Digest 2001, pages 655-658	

**Examiner Signature** \_\_\_\_\_ **Date Considered** \_\_\_\_\_

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup>Applicant's unique citation designation number (optional). <sup>2</sup>See Kind Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov). MPEP 101.04 or follow the hyperlink from the title of the document to the intranet. <sup>3</sup>Enter Office that issued the document, by the two-letter code (WIPO Standard ST. 3). <sup>4</sup>For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup>Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup>Applicant is to indicate here if English language Translation is attached.